



Sleepy Keeper : a New Approach to Low-Leakage Power VLSI Design

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Outline

- Introduction
- Related work
- Sleepy Keeper
- Experimental Methodology
- Experimental Results
- Conclusion

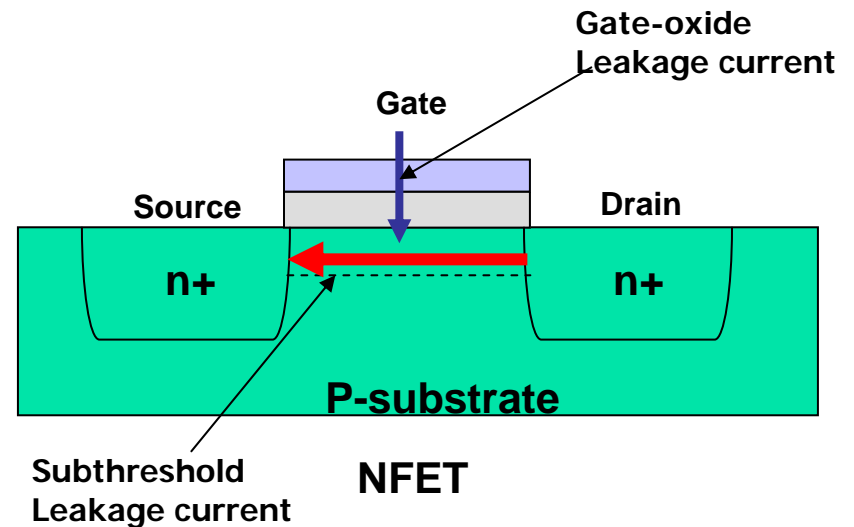


Background

- Technology Trend
 - High density → Transistor size scaling down
 - High performance → V_{th} scaling down
 - ➔ Increase of leakage power
- Increase of portable device (e.g., Cell phone, PDA)
- Power Consumption = Dynamic + Static
- Static Power Consumption (Leakage Power) became a significant issue

Leakage Power

- Gate-oxide leakage
 - Gate tunneling due to thin oxide
- Subthreshold leakage
 - Scaling down of V_{th}
 - Short-channel effect
 - Our research focus





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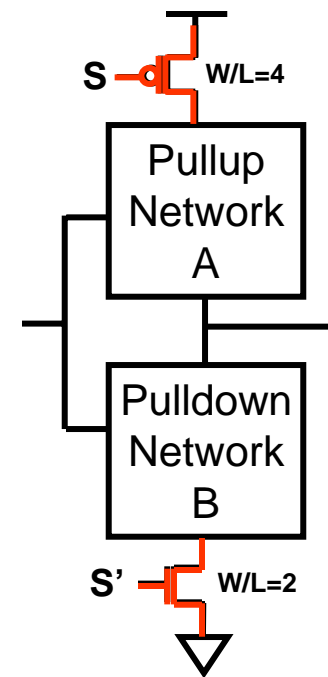


Previous Work

- Sleep
- ZigZag
- Stack
- Sleepy-Stack
- Leakage Feedback

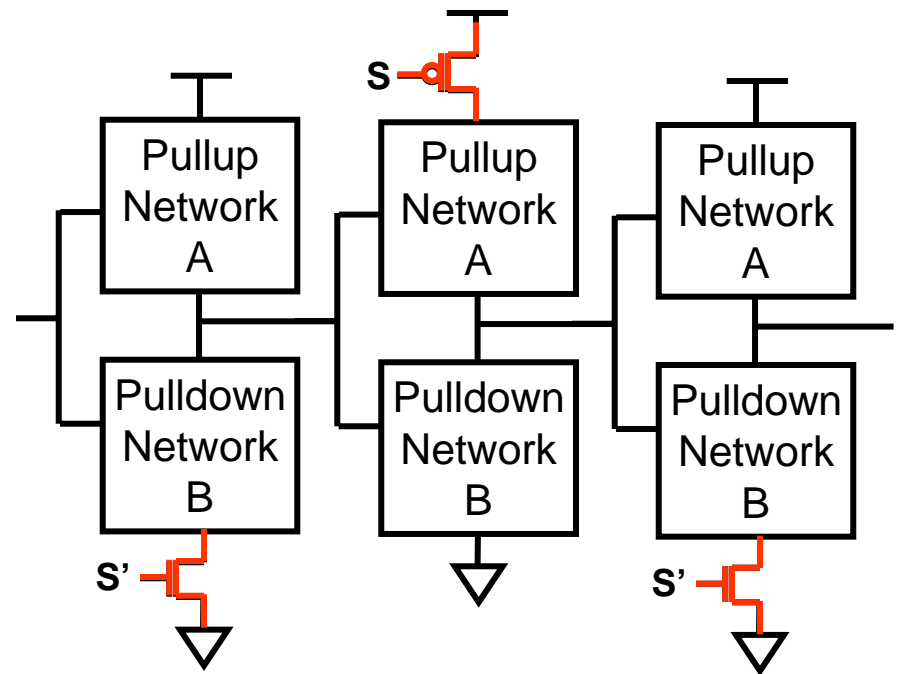
Approaches : Sleep

- Source gating
- State destructive
Floating output
- Additional routing
- Dual V_{th} applicable



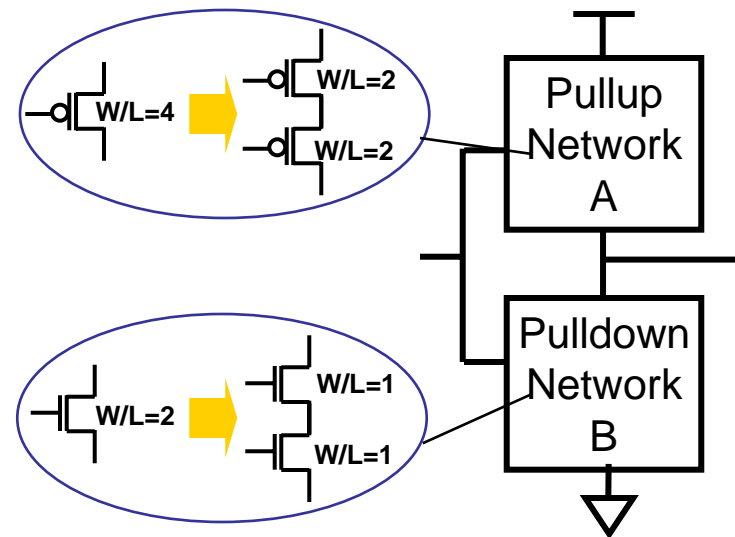
Approaches : Zigzag

- Favored input vector
 - Reduced wake-up overhead than sleep approach
- State destructive
- Dual V_{th} applicable



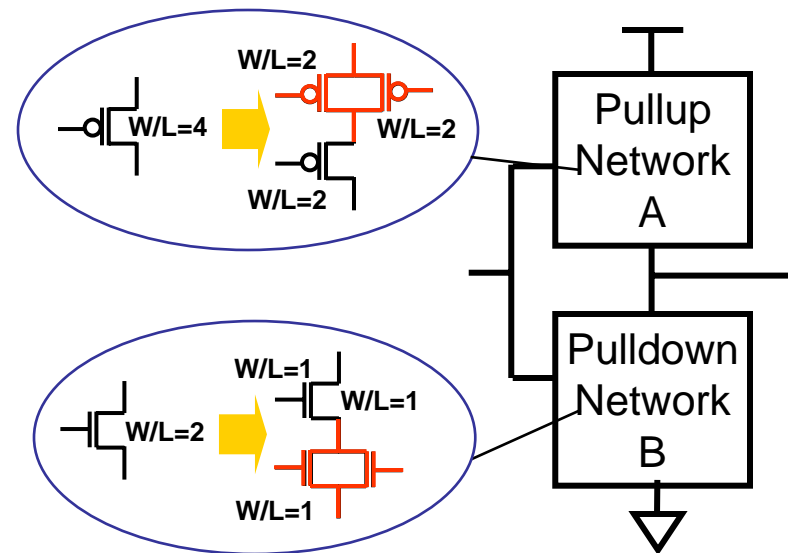
Approaches : Stack

- Duplicated transistors
 - Induce reverse bias in cutoff
- State-Saving
- Delay penalty
 - greater gate capacitance
 - greater resistance



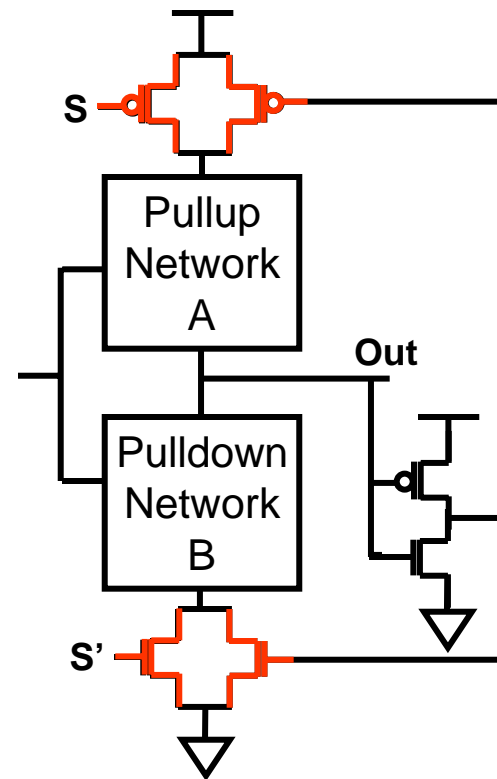
Approaches : Sleepy-Stack

- Combination of Sleep and Stack
Source gating, Stack effect
- State-saving
- Ultra-low leakage
- Area penalty



Approaches : Leakage Feedback

- Based on Sleep approach
- State-saving
- Leakage in inverter
- Area penalty





Outline

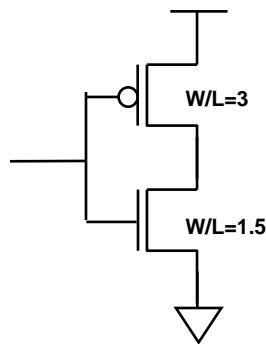
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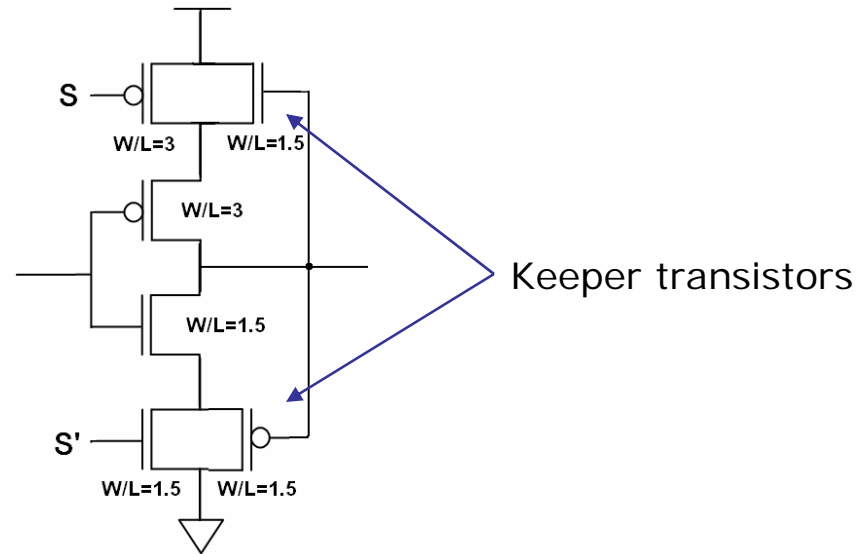
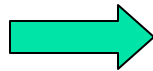
Motivation of Sleepy Keeper

- Ultra low leakage with dual V_{th}
- State-saving
- Less area penalty and faster than sleepy stack approach

Sleepy Keeper Structure



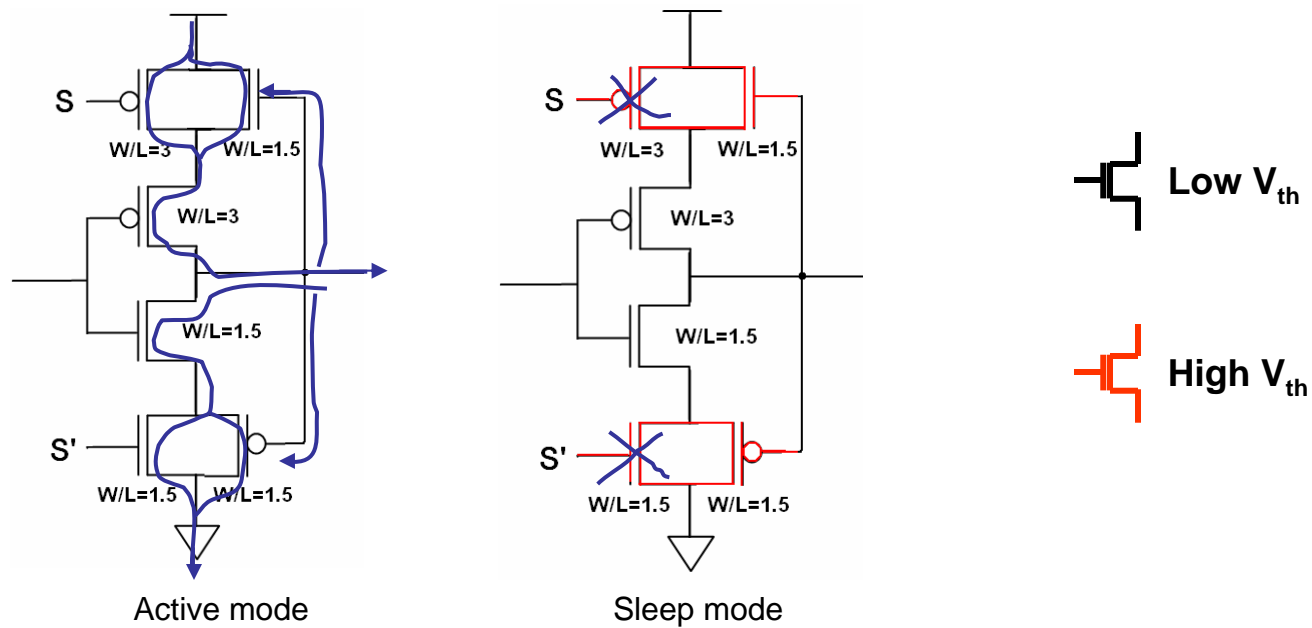
Conventional CMOS inverter



Sleepy keeper inverter

- Add sleep transistors
- Add two transistors driven by output
NMOS to Pull-up Network, PMOS to Pull-down Network

Sleepy Keeper Operation



- During active mode, sleep transistors are on
→ reducing delay
- During sleep mode, sleep transistors are off
→ saving state
- Can apply dual V_{th}



Sleepy Keeper Operation

- Assumptions
 - Small delay between active mode and sleep mode
- Keeper transistors
 - keeper transistors are not for switching
 - lower voltage can be applied to maintain state



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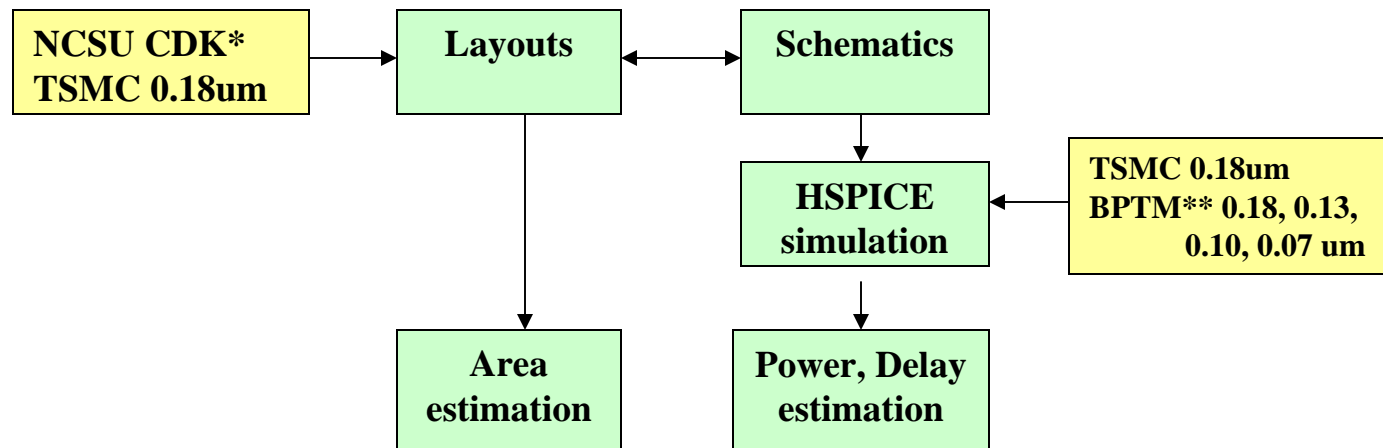


Experimental Methodology

- Seven techniques are compared
base case, forced stack, sleep, zigzag,
sleepy stack, leakage feedback, and
sleepy keeper
- Dual- V_{th} applied for sleep, zigzag,
sleepy stack, leakage feedback, and
sleepy keeper
Dual- V_{th} applied (0.2V and 0.4V)

Experimental Methodology

- Worst-case propagation delay, static power and dynamic power for each approach measured
- Area estimated by scaling down 0.18um layout

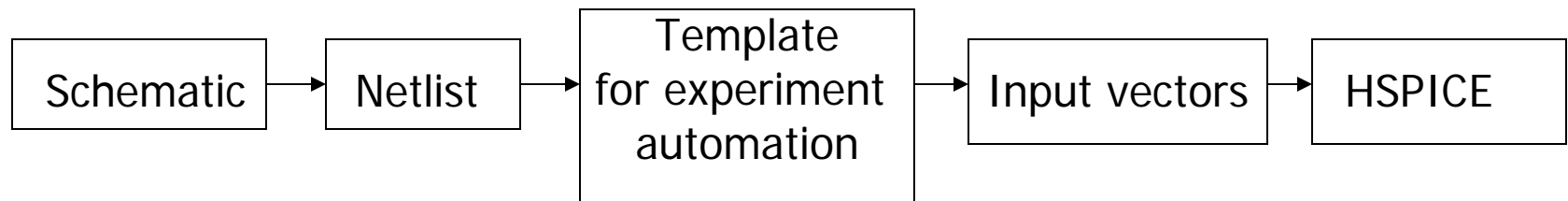


*NC State University Cadence Design Kit
[Online]. Available <http://www.cadence.ncsu.edu>.

**Berkeley Predictive Technology Model (BPTM)
[Online]. Available <http://www.eas.asu.edu/~ptm>.

Experimental Methodology

- Power, delay estimation



- Area estimation

Scaled by ratio of squares & 10% overhead for nonlinear scaling layers

Ex) $100\mu\text{m}^2$ in TSMC $0.18\mu\text{m}$

For $0.10\mu\text{m} \Rightarrow 100 * (0.10^2/0.18^2) * 1.1$

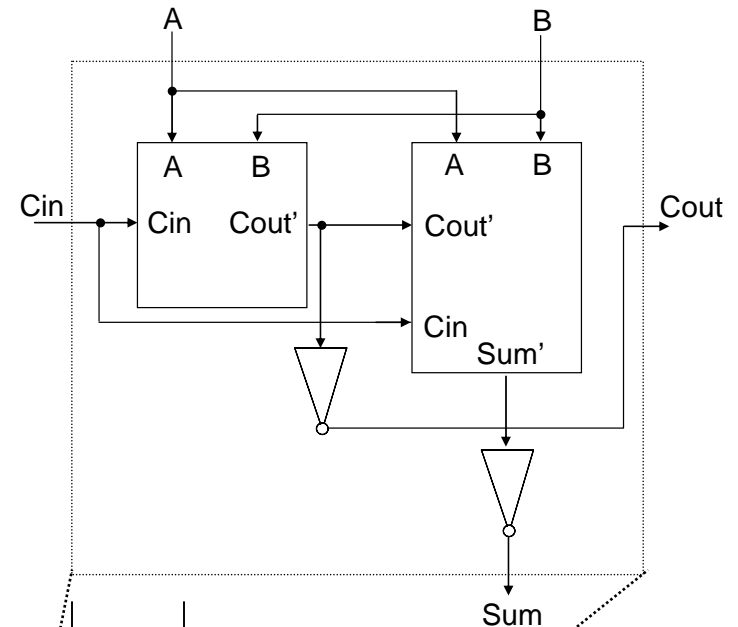
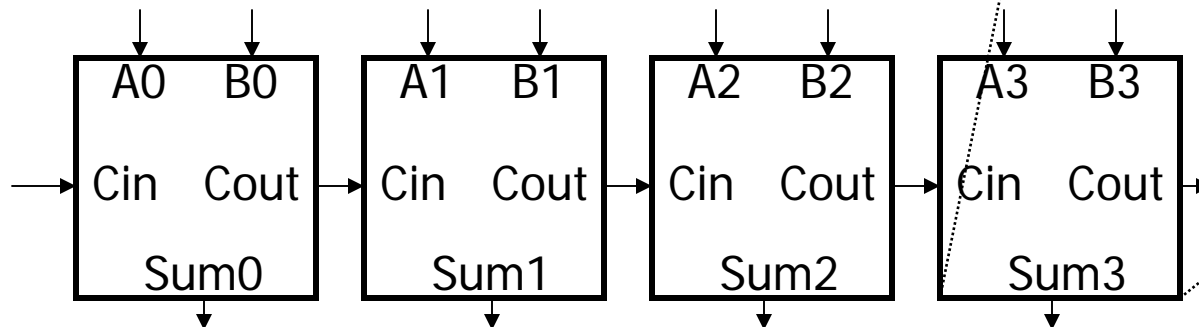
Test circuit (4-bit adder chain)

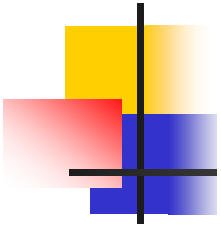
- 1-bit adder

$$Cout = AB + Cin(A+B)$$

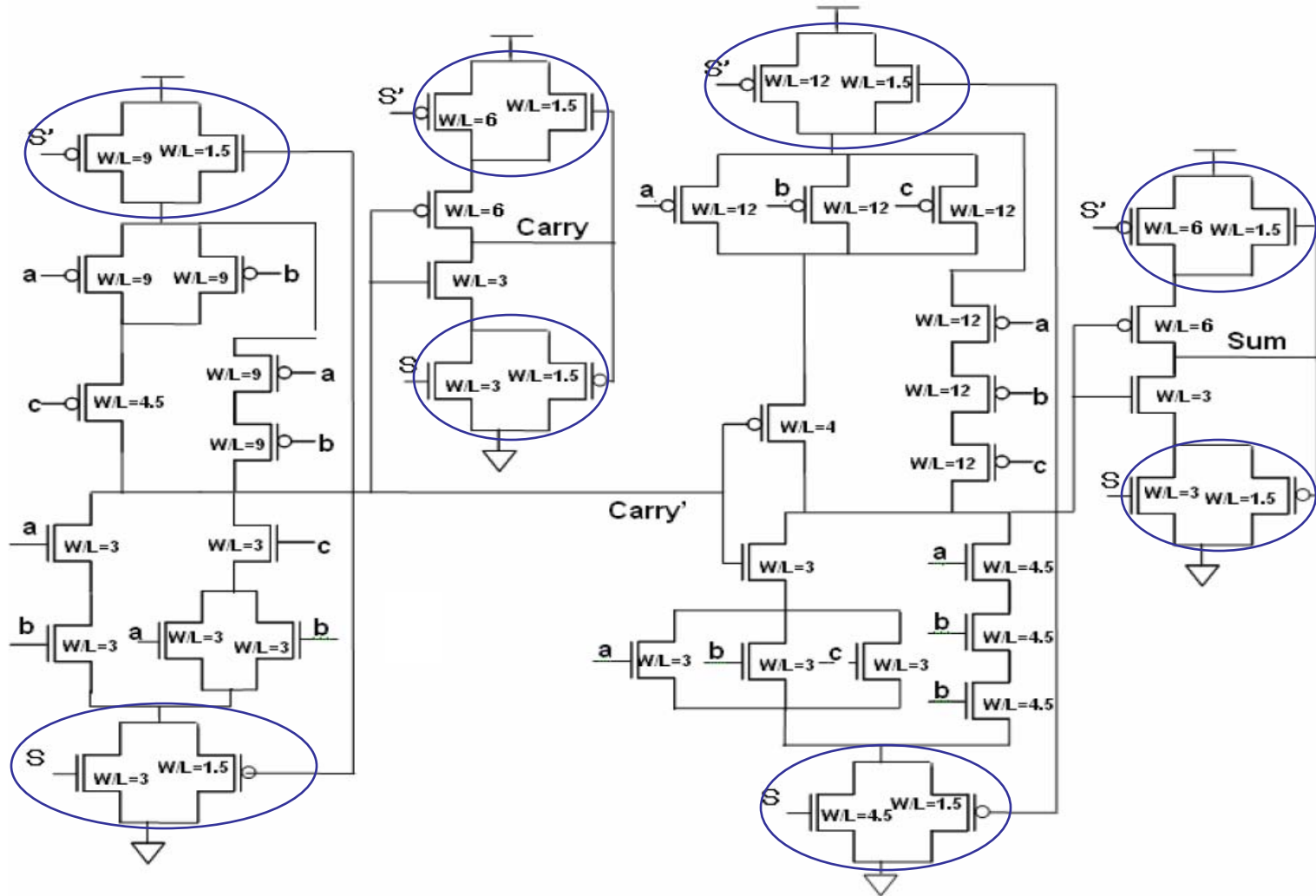
$$Sum = ABCin + (A+B+Cin)Cout'$$

- 4-bit adder chain





1-bit adder schematic

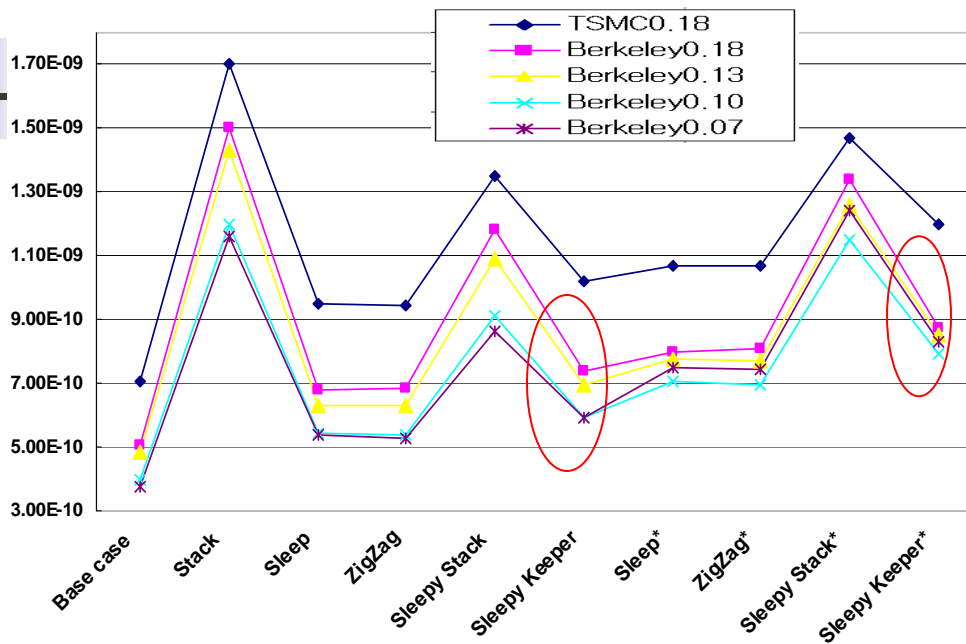




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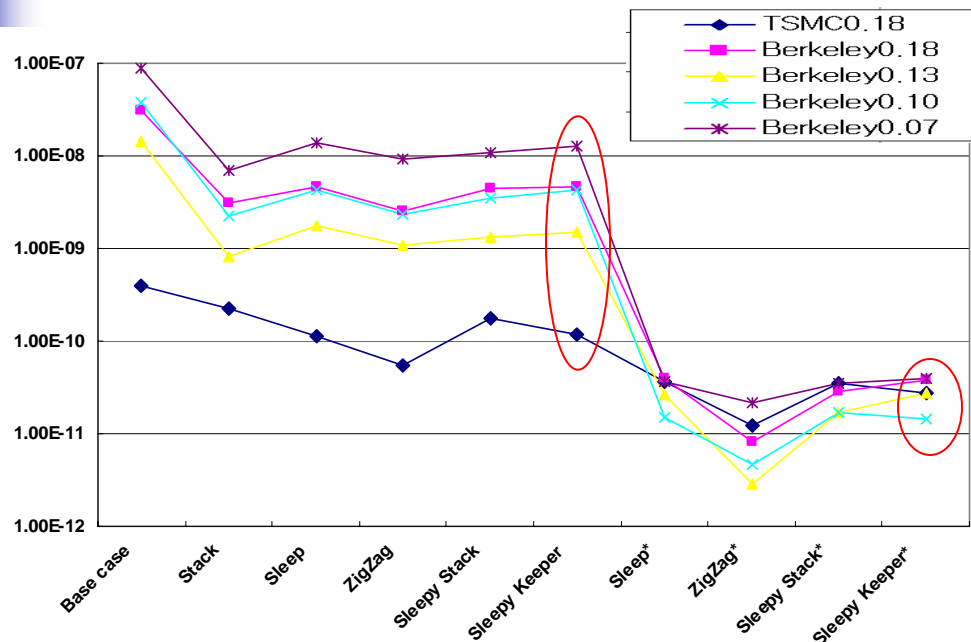
4-bit adder results – Propagation Delay



0.07μ	
Base case	3.76E-10
Stack	1.16E-09
Sleep	5.38E-10
ZigZag	5.25E-10
Sleepy Stack	8.64E-10
Sleepy Keeper	5.90E-10
Sleep*	7.52E-10
ZigZag*	7.43E-10
Sleepy Stack*	1.24E-09
Sleepy Keeper*	8.30E-10

- Compared mainly to sleepy stack (best prior leakage control technique while state saving)
- Sleepy keeper results 46% less delay than sleepy stack (49% less when dual Vth)
- Reason : Less number of transistors than sleepy stack

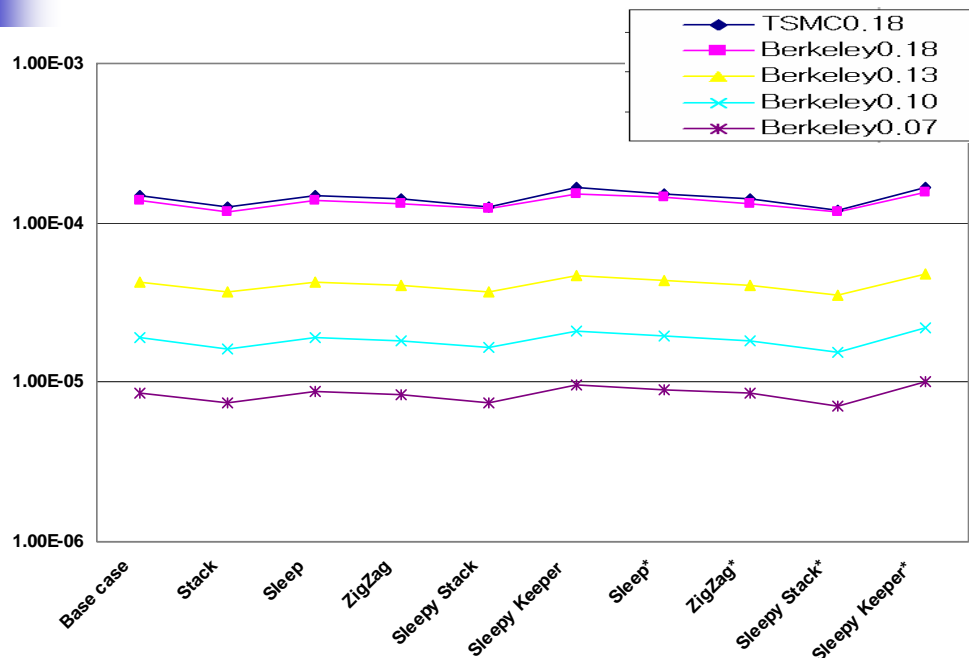
4-bit adder results – Static Power



0.07μ	
Base case	8.90E-08
Stack	6.83E-09
Sleep	1.36E-08
ZigZag	9.09E-09
Sleepy Stack	1.08E-08
Sleepy Keeper	1.30E-08
Sleep*	3.65E-11
ZigZag*	2.19E-11
Sleepy Stack*	3.50E-11
Sleepy Keeper*	3.89E-11

- Compared to stack, sleepy keeper reduce leakage power 175X
- Sleepy keeper results 20% more static power than sleepy stack (11% more when dual V_{th})

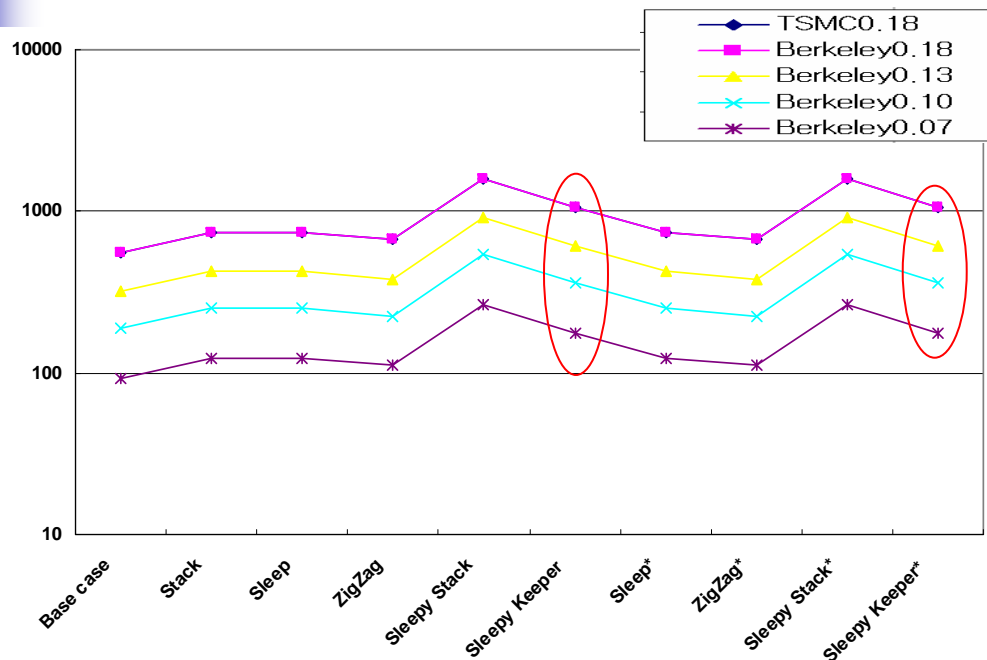
4-bit adder results – Dynamic Power



0.07μ	
Base case	8.63E-06
Stack	7.41E-06
Sleep	8.77E-06
ZigZag	8.37E-06
Sleepy Stack	7.39E-06
Sleepy Keeper	9.76E-06
Sleep*	9.03E-06
ZigZag*	8.46E-06
Sleepy Stack*	7.06E-06
Sleepy Keeper*	1.00E-05

- Compared to sleepy stack, sleepy keeper results 31% more dynamic power (41% more when dual Vth)
- Conjecture : more short circuit current

4-bit adder results – Area



0.07 μ	
Base case	91.84
Stack	123.76
Sleep	123.76
ZigZag	110.48
Sleepy Stack	263.52
Sleepy Keeper	177.11

- 93% larger than base case, 49% smaller than sleepy stack
- Reason : Sleep transistors, additional 2 transistors, and unusual placement of keeper transistor



Conclusion

- Ultra low static power with dual V_{th}
- State saving
- Less area, less delay than sleepy stack
- Dynamic power increased